

In the Claims:

1.-25. (Cancelled)

26. (Currently Amended) A method of forming a semiconductor device, the method comprising:

providing a substrate;

forming a first interlayer dielectric on the substrate;

forming a capacitor contact pad located in the first interlayer dielectric in a first region;

forming a second interlayer dielectric on the first interlayer dielectric;

forming an integrated capacitor having a first top electrode and a first bottom electrode formed in the second interlayer dielectric such that the first bottom electrode is in electrical contact with the capacitor contact pad, at least a portion of the integrated capacitor being positioned directly over the capacitor contact pad; and

forming a capacitor contact pad contact through the second interlayer dielectric providing an electrical connection to the capacitor contact pad, at least a portion of the capacitor contact pad contact being positioned directly over the capacitor contact pad, wherein a portion of the capacitor contact pad directly under the integrated capacitor and a portion of the capacitor contact pad directly under the capacitor contact pad contact form a continuous contact region.

27. (Original) The method of claim 26, further comprising forming a device on a second region of the substrate before forming the first interlayer dielectric.

28. (Original) The method of claim 27, wherein the device is a transistor.

29. (Previously presented) The method of claim 28, further comprising simultaneously forming a contact in the first interlayer dielectric when the step of forming a capacitor contact pad is performed, wherein the contact is electrically connected to the transistor.

30. (Original) The method of claim 29, further comprising simultaneously forming a storage capacitor in the second interlayer dielectric when the step of forming the integrated capacitor is performed, wherein the storage capacitor has a second top electrode and a second bottom electrode formed such that the second bottom electrode is in electrical contact with the transistor via the contact.

31. (Previously presented) The method of claim 29, wherein the capacitor contact pad and the contact are formed of a first material.

32. (Original) The method of claim 31, wherein the first material is a material selected from the group consisting of a metal, an elemental metal, a transition metal, and a combination thereof.

33.-35. (Cancelled)

36. (Currently Amended) A method of forming a semiconductor device, the method comprising:

providing a substrate having at least one first region and one second region;

forming a transistor on the first region;

forming a first interlayer dielectric over the substrate;

forming a capacitor contact pad in the first interlayer dielectric upon the second region, the capacitor contact pad being a thickness substantially equivalent to the thickness of the first interlayer dielectric;

forming a second interlayer dielectric on the first interlayer dielectric;

forming an integrated capacitor in the second interlayer dielectric upon the second region and a storage capacitor in the second interlayer dielectric upon the first region, the integrated capacitor having a first bottom electrode being in electrical contact with the capacitor contact pad and the storage capacitor having a second bottom ~~electrode, the electrode,~~ the second bottom electrode being in electrical contact with the transistor, at least a portion of the integrated capacitor is positioned directly over the capacitor contact pad; and

forming a capacitor contact pad contact in the second dielectric layer, at least a portion of the capacitor contact pad contact being in electrical contact with the capacitor contact pad and positioned directly over the capacitor contact pad, wherein a portion of the capacitor contact pad directly under the integrated capacitor and a portion of the capacitor contact pad directly under the capacitor contact pad contact form a continuous contact region.

37. (Previously presented) The method of claim 36, further comprising simultaneously forming a transistor contact in the first interlayer dielectric when the step of forming the capacitor contact pad is performed, wherein the transistor contact electrically connects a source/drain of the transistor with the second bottom electrode.

38. (Previously presented) The method of claim 37, wherein the transistor contact and the capacitor contact pad are formed of a first material.

39. (Original) The method of claim 38, wherein the first material is a material selected from the group consisting of a metal, an elemental metal, a transition metal, and a combination thereof.

40. (Previously presented) The method of claim 36, wherein the capacitor contact pad is formed of a material selected from the group consisting of a metal, an elemental metal, a transition metal, and a combination thereof.

41. (Previously presented) The method of claim 36, wherein forming the capacitor contact pad includes forming a barrier layer on the first interlayer dielectric and forming a conductive layer on the barrier layer.

42. (Original) The method of claim 41, wherein the barrier layer is formed of a material selected from the group consisting of titanium, titanium nitride, and combinations thereof.

43. (Original) The method of claim 41, wherein the conductive layer comprises tungsten.

44.-57. (Cancelled)